High Response Silicon Avalanche Photodiode Receiver

CMC Electronics' 264-339829 series use a Silicon APD with a built-in preamplifier, enabling optimum signal-to-noise performance.

The APD is coupled to a GaAs FET input trans-impedance amplifier in a 12-lead TO-8 package. The amplifier has an overload input protection circuit which sustains high optical power exposure with a very fast recovery time (-001).

The internal temperature can be monitored via an embedded thermal sensor located close to the APD. The module is designed with a 10 Ω output impedance and can be AC- or DC-coupled.

Customizations such as bandwidth selection, NEP screening, responsivity optimization and packaging are available upon request.

Features

- 500 µm Silicon APD
- 60 – 100 MHz Preamplifier Module
- Spectral Response: 550-1100nm
- Low Noise Equivalent Power (NEP)
- Fast Overload Recovery
- Hermetically Sealed TO-8 Package
- ROHS compliant
- ITAR free

Applications

- Range Finding
- LIDAR
- Instrumentation
- Laser Profiling
- Industrial
- Photometry

Table 1. Electro-Optical Characteristics

Unless otherwise specified: T_A = 25°C, V+ = 5 V, V-=-5 V, R_L = 100 Ω, λ = 1064 nm +/- 10 nm (Externally AC coupled through 4.7µF)

Parameter	Min.	Typ.	Max.	Units
Active area		500		µm
Operating Voltage (Note 1)	150	225	300	V
Temperature coefficient of V_{OP}		0.6	1.5	V/˚C
ADP dark current		7	50	nA
Responsivity	1000			kV/W
Noise equivalent power (Note 2)				
1064 nm [T_{case}=25°C]		100	120	fW/√Hz
1604 nm [T_{case}=70°C]		220	475	fW/√Hz
Output impedance		10		Ω
Bandwidth	60	80		MHz
Rise time (10-90%)		6		ns
Fall time (90-10%)		6		ns
Linear output voltage swing (Pulse)	1.5	2.5	4.0	V
Output offset voltage	-0.75	-0.45	0	V
Thermal sensor (in option)				mV
Overload recovery for optical power input signal of 1 mW, 20 ns pulse width:				
V_{out} → 200 ns after pulse start			300	mV
V_{out} → 1 µs after pulse start			20	mV
Hybrid Supply current V_POS (pin 10)	25	30	40	mA
V_NEG (pin 11)	-20	-15	-10	mA

Notes:
1. Each APD receivers will have its individual V_{OP} (provided on its production tests report).
2. NEP values for +85°C are by design and are for reference only. No test values provided on individual test reports. Integration of the noise calculation is based on minimum bandwidth.

Table 2. Absolute-Maximum Ratings, Limiting Values

Parameter	Min.	Max.	Units
APD breakdown, Maximum voltage [HV_POS (pin7)] (Note 1)		450	V
Recommended overcurrent limit		100	µA
Input Voltage Positive Supply [V_POS (+5V) (pin10)] (Note 2)	+4.8	+6.0	V
Input Voltage Negative Supply [V_NEG (-5V) (pin11)] (Note 2)	-4.8	-6.0	V
Maximum Optical Power, M = 100		300	µW
Maximum Optical Power, M = 1		30	mW
Operating Temperature	-20	70	°C
Storage Temperature	-55	125	°C

Note:
1. Absolute maximum over the product Temperature Operating Range (-40°C to +85°C).
2. Assuming light spreads uniformly over APD's active area.

Figure 1. CMC 264-339829 Series block diagram

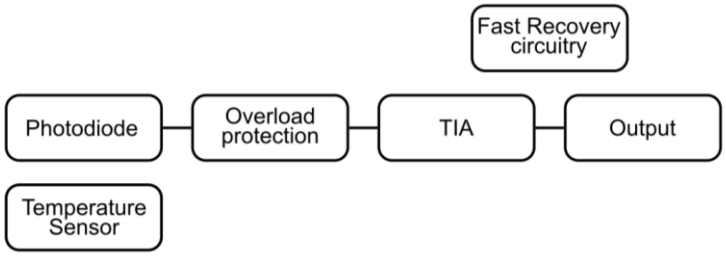
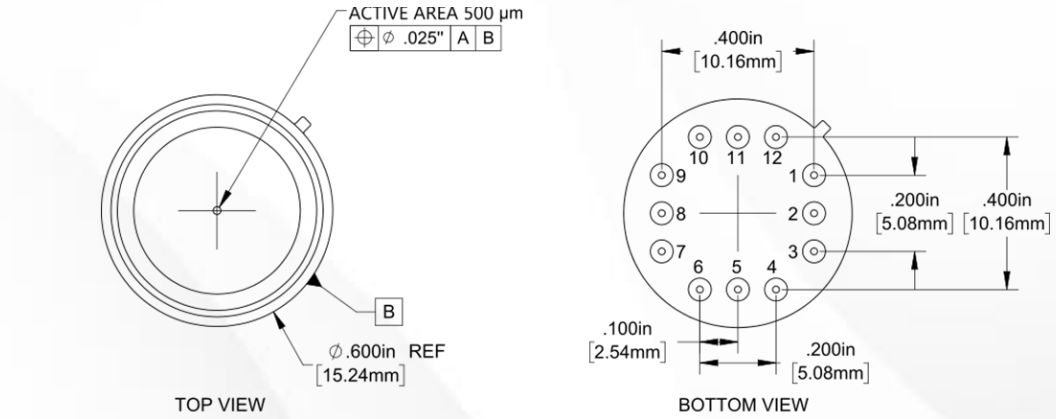
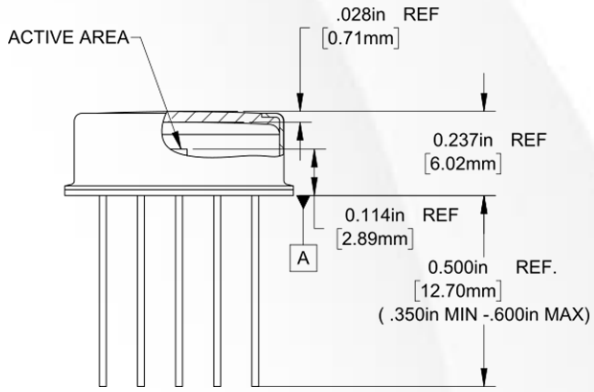


Figure 2. Package Dimension and Pinout

Unless otherwise specified, dimensions are in inches [mm] and are for reference only.





1	GND	7	HV_POSITIVE
2	GND	8	GND
3	GND	9	OUTPUT
4	T sensor (option)	10	V_POS (+5V)
5	T sensor (option)	11	V_NEG (-5V)
6	GND	12	GND

VAR Options

-001	Silicon APD 500 µm, 60-100 MHz TIA, with fast recovery

For more information, visit www.cmcelectronics.ca/optoelectronics
Or email us at opto@cmcelectronics.ca

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